

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>C</sub> = +25°C
100V	57mΩ @ V <sub>GS</sub> = 10V	20A
	71mΩ @ V <sub>GS</sub> = 6V	18A
	96mΩ @ V <sub>GS</sub> = 4.5V	16A

## Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> – Minimizes On State Losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

## Description and Applications

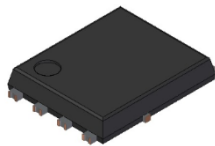
This new generation N-Channel Enhancement Mode MOSFET is designed to minimize R<sub>DS(ON)</sub> yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switches.

- DC-DC converters
- Load switches

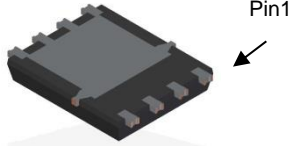
## Mechanical Data

- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.097 grams (Approximate)

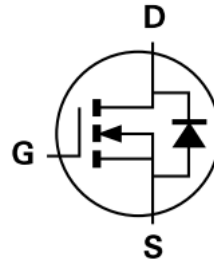
PowerDI5060-8 (SWP) (Type UX)



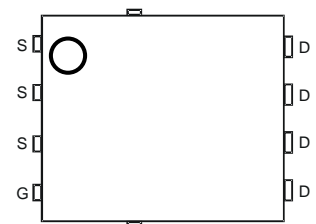
Top View



Bottom View



Internal Schematic



Top View  
Pin Configuration

## Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Quantity	Carrier
DMTH10H072LPS-13	PowerDI5060-8 (SWP) (Type UX)	2,500	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



D D D D = Manufacturer's Marking  
 TH1H72LS = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY or YY = Year (ex: 23 = 2023)  
 WW = Week (01 to 53)

**Maximum Ratings** (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	100	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 7)	Steady State	T <sub>C</sub> = +25°C	I <sub>D</sub>	20	A
		T <sub>C</sub> = +100°C		14	
Maximum Continuous Body Diode Forward Current (Note 7)			I <sub>S</sub>	20	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	80	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I <sub>SM</sub>	80	A
Avalanche Current, L = 0.1mH (Note 8)			I <sub>AS</sub>	6	A
Avalanche Energy, L = 0.1mH (Note 8)			E <sub>AS</sub>	1.8	mJ

**Thermal Characteristics** (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	98	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	3.0	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	49	°C/W
Total Power Dissipation (Note 7)	T <sub>C</sub> = +25°C	P <sub>D</sub>	51.7	W
Thermal Resistance, Junction to Case (Note 7)		R <sub>θJC</sub>	2.9	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 9)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 9)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	—	3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	44	57	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.5A
		—	54	71		V <sub>GS</sub> = 6V, I <sub>D</sub> = 4A
		—	73	96		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2.6A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS (Note 10)</b>						
Input Capacitance	C <sub>iSS</sub>	—	266	—	pF	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	87.2	—		
Reverse Transfer Capacitance	C <sub>rSS</sub>	—	3.6	—		
Gate Resistance	R <sub>g</sub>	—	7.0	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	2.8	—	nC	V <sub>DS</sub> = 50V, I <sub>D</sub> = 4.5A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	5.1	—		
Gate-Source Charge	Q <sub>gs</sub>	—	0.8	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	1.7	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.0	—	ns	V <sub>DD</sub> = 50V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.5A, R <sub>G</sub> = 3Ω
Turn-On Rise Time	t <sub>R</sub>	—	2.8	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	9.5	—		
Turn-Off Fall Time	t <sub>F</sub>	—	3.2	—		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	37.5	—	ns	I <sub>S</sub> = 4.5A, di/dt = 300A/µs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	86.8	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

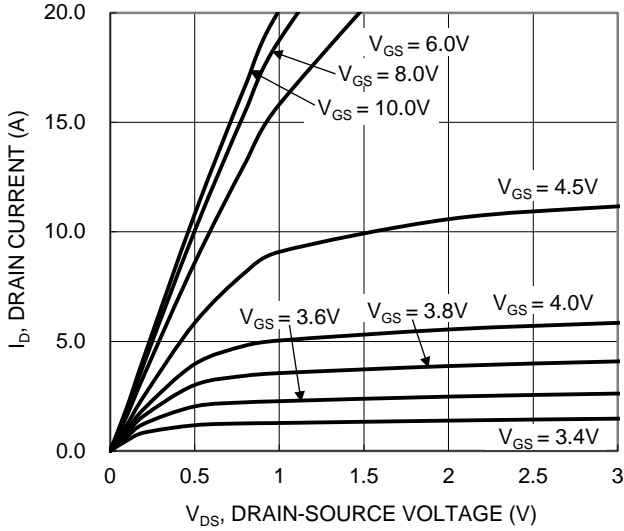


Figure 1. Typical Output Characteristic

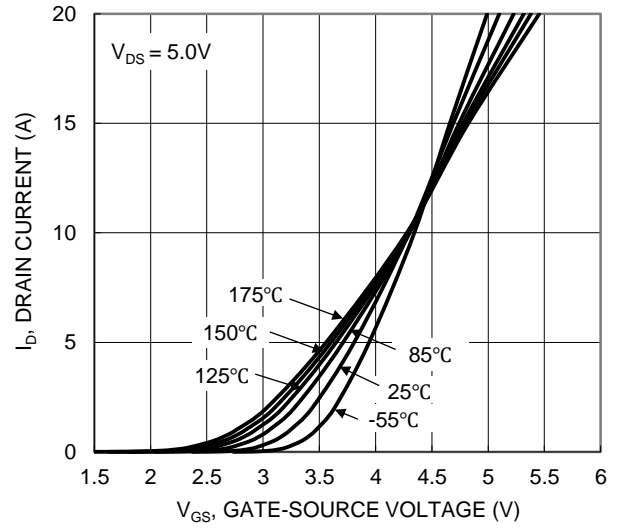


Figure 2. Typical Transfer Characteristic

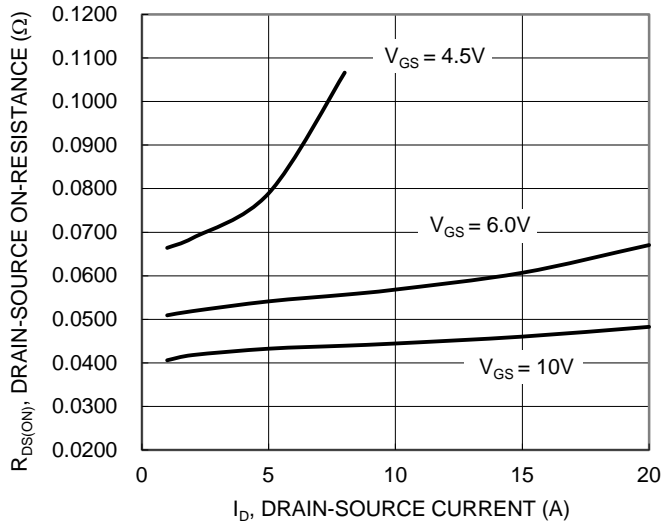


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

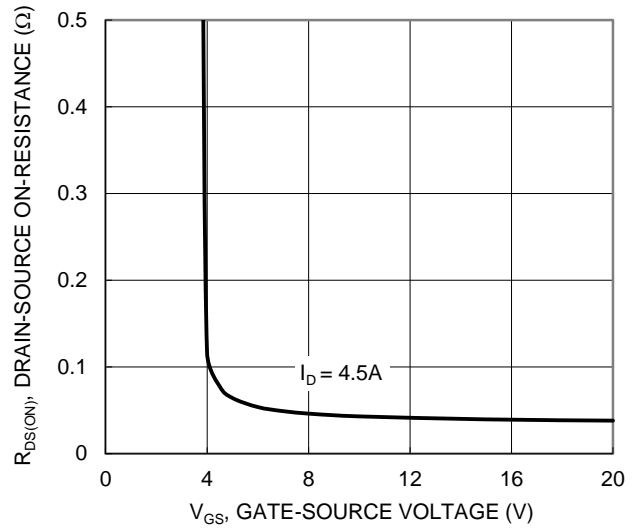


Figure 4. Typical Transfer Characteristic

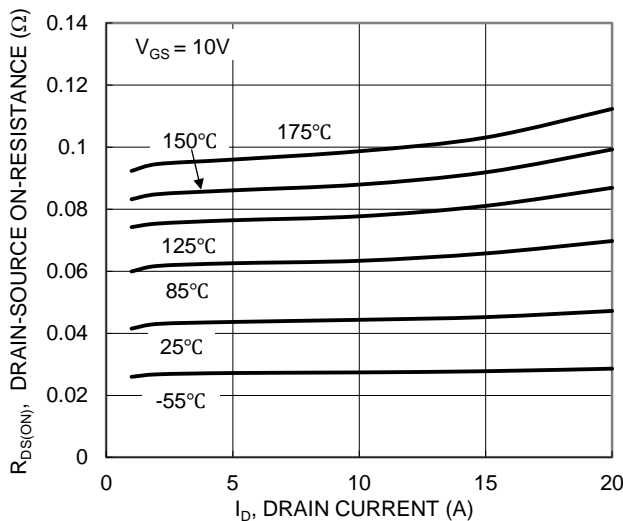


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

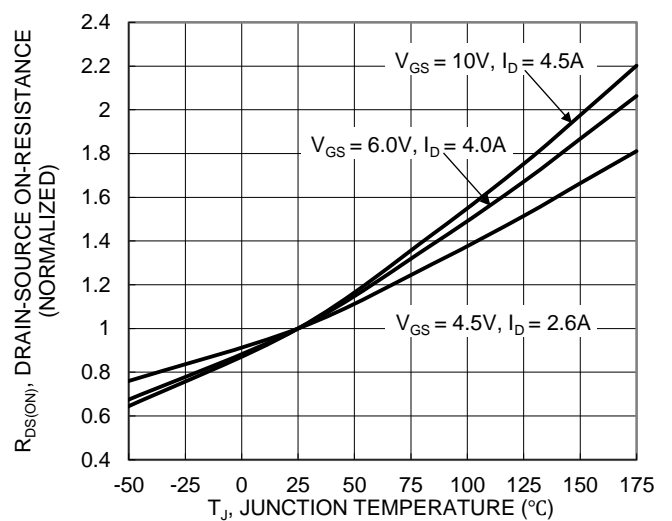


Figure 6. On-Resistance Variation with Temperature

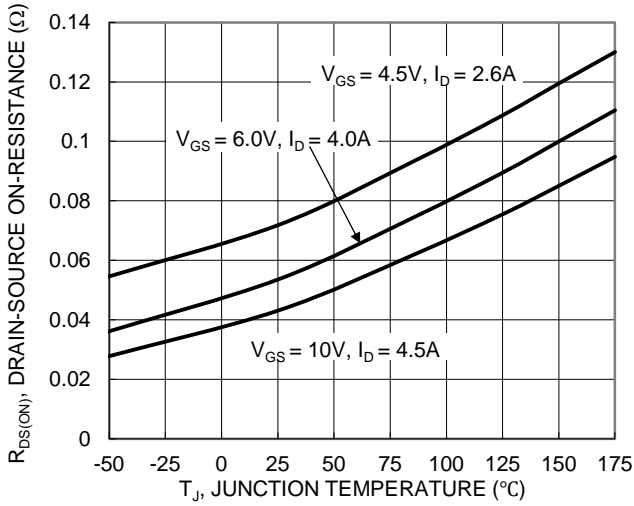


Figure 7. On-Resistance Variation with Temperature

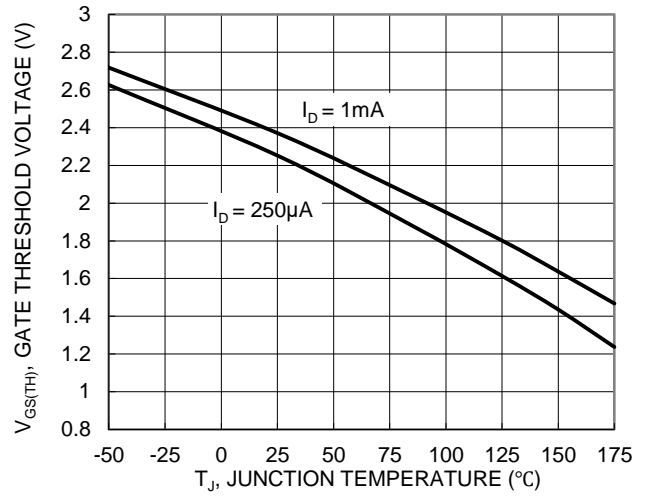


Figure 8. Gate Threshold Variation vs. Junction Temperature

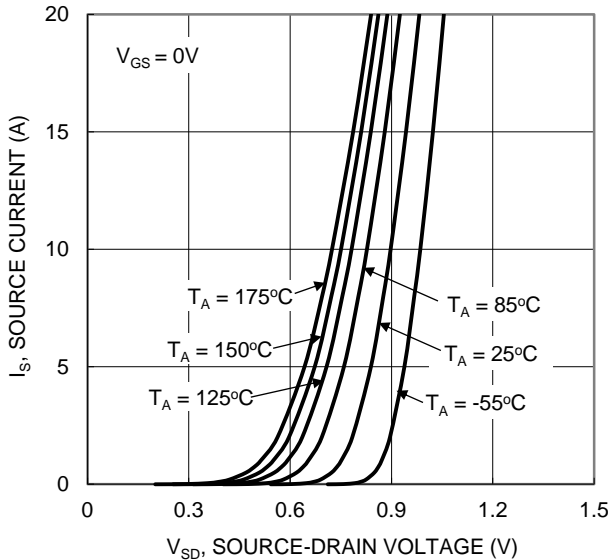


Figure 9. Diode Forward Voltage vs. Current

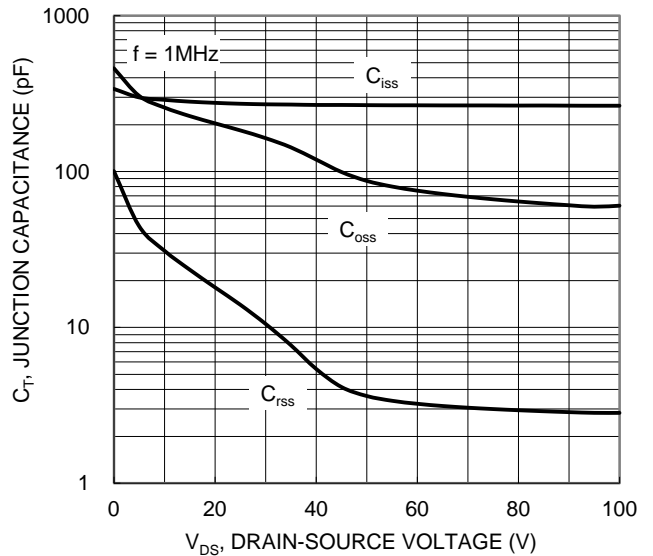


Figure 10. Typical Junction Capacitance

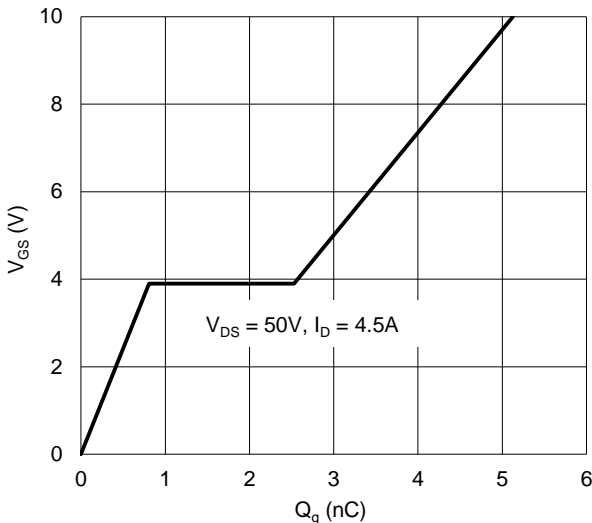


Figure 11. Gate Charge

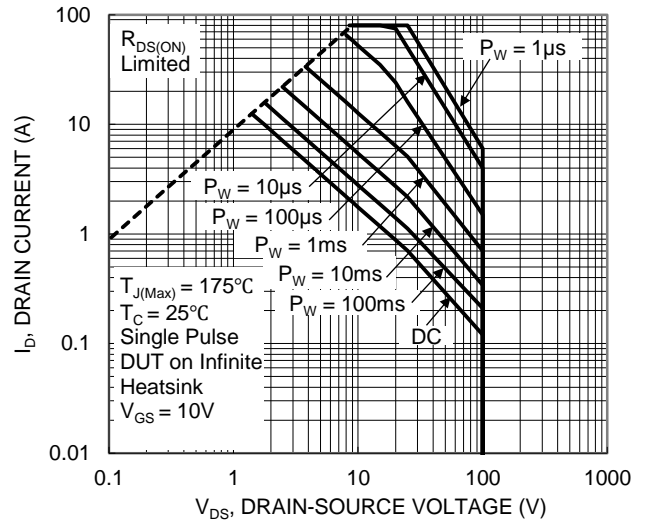
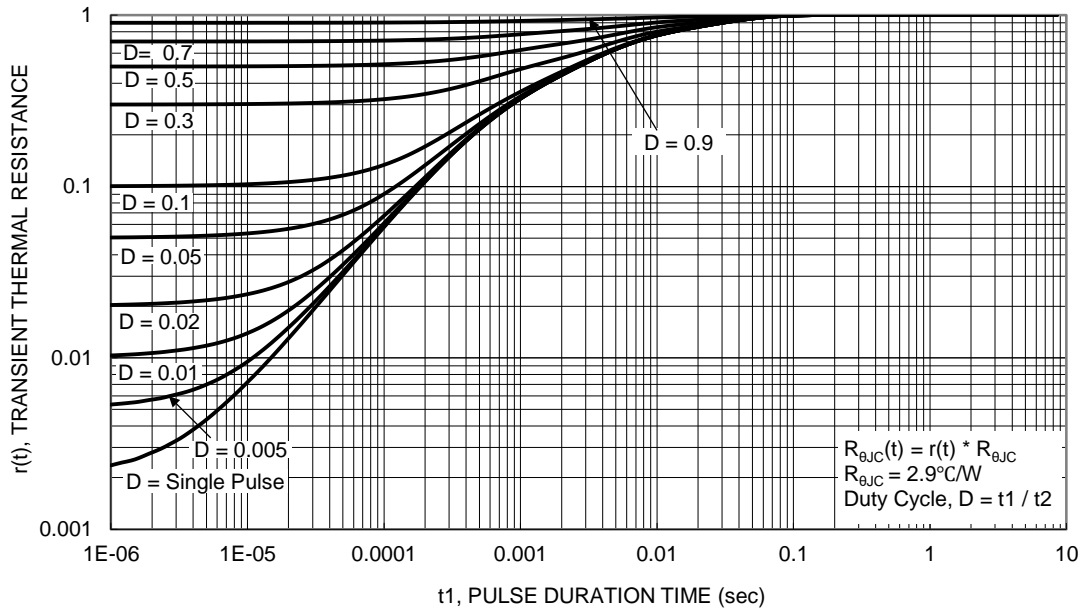


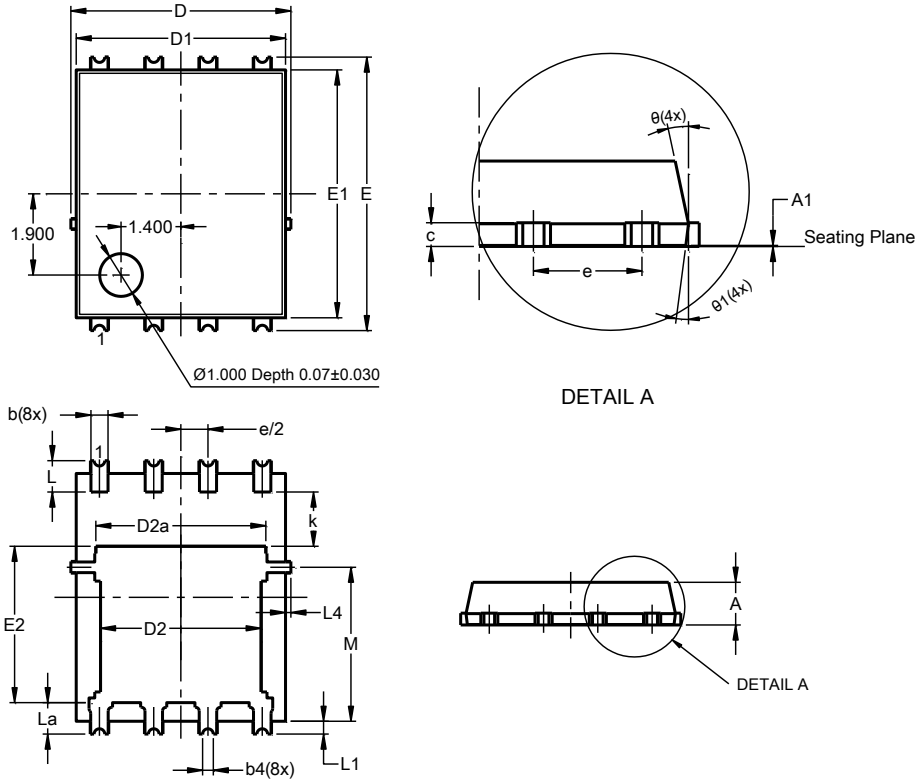
Figure 12. SOA, Safe Operation Area



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8 (SWP) (Type UX)**

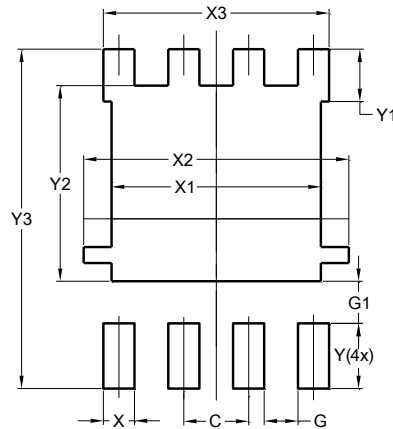


PowerDI5060-8 (SWP) (Type UX)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8(SWP) (Type UX)**



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	5.190
X3	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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